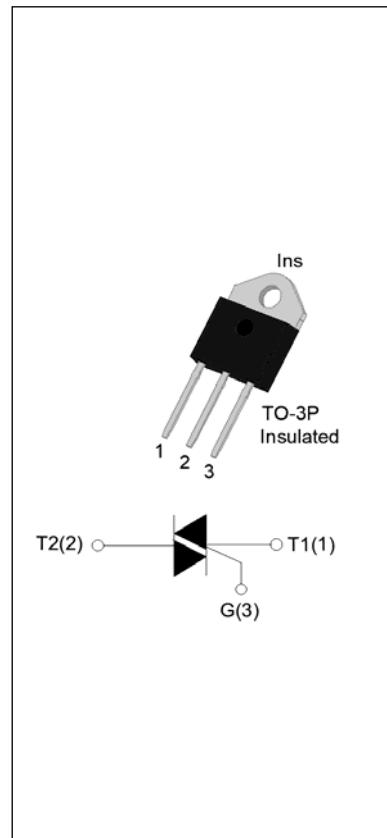


**DESCRIPTION:**

The T3035H-6Z triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T3035H-6Z provides a very high switching capability up to junction temperatures of 150°C. By using an internal ceramic pad, T3035H-6Z provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-3P is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	30	A
V_{DRM} / V_{RRM}	600	V
$I_{GT\text{ I/II/III}}$	35/35/35	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-150	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600	V
RMS on-state current ($T_c \leq 114^\circ\text{C}$)	$I_{T(RMS)}$	30	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	270	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		297	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	365	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=150^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=150^\circ\text{C}$)	I_{GM}	4	A

Average gate power dissipation ($T_j=150^\circ\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	1	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D = 12\text{V}$ $R_L = 33\Omega$	I - II - III	MAX.	35	mA
V_{GT}		I - II - III	MAX.	1.3	V
V_{GD}	$V_D = V_{DRM}$ $T_j = 150^\circ\text{C}$ $R_L = 3.3\text{k}\Omega$	I - II - III	MIN.	0.15	V
I_L	$I_G = 1.2I_{GT}$	I - III	MAX.	70	mA
		II		80	
I_H	$I_T = 500\text{mA}$		MAX.	50	mA
dV/dt	$V_D = 400\text{V}$ Gate Open $T_j = 150^\circ\text{C}$		MIN.	1200	V/ μs
$(dI/dt)c$	$(dV/dt)c = 20\text{V}/\mu\text{s}$, $T_j = 150^\circ\text{C}$		MIN.	18	A/ms
t_{on}	$I_G = 40\text{mA}$ $I_A = 200\text{mA}$ $I_R = 20\text{mA}$ $T_j = 25^\circ\text{C}$	TYP.	10	μs	
t_{off}			80		

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM} = 42\text{A}$	$t_p = 380\mu\text{s}$	$T_j = 25^\circ\text{C}$	1.5
V_{TO}	Threshold voltage		$T_j = 150^\circ\text{C}$	0.7
R_D	Dynamic resistance		$T_j = 150^\circ\text{C}$	$\text{m}\Omega$
I_{DRM}	$V_D = V_{DRM}$	$V_R = V_{RRM}$	$T_j = 25^\circ\text{C}$	5
			$T_j = 150^\circ\text{C}$	5
I_{RRM}				mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	0.85	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	50	$^\circ\text{C}/\text{W}$

ORDERING INFORMATION

T	30	35	H	-6	Z
Triacs					Z:TO-3P(Ins)
	<u>$I_T(\text{RMS}):30\text{A}$</u>				<u>$6:V_{DRM} / V_{RRM} \geq 600\text{V}$</u>
		<u>$35:I_{GT1-3} \leq 35\text{mA}$</u>			<u>High junction temperature</u>

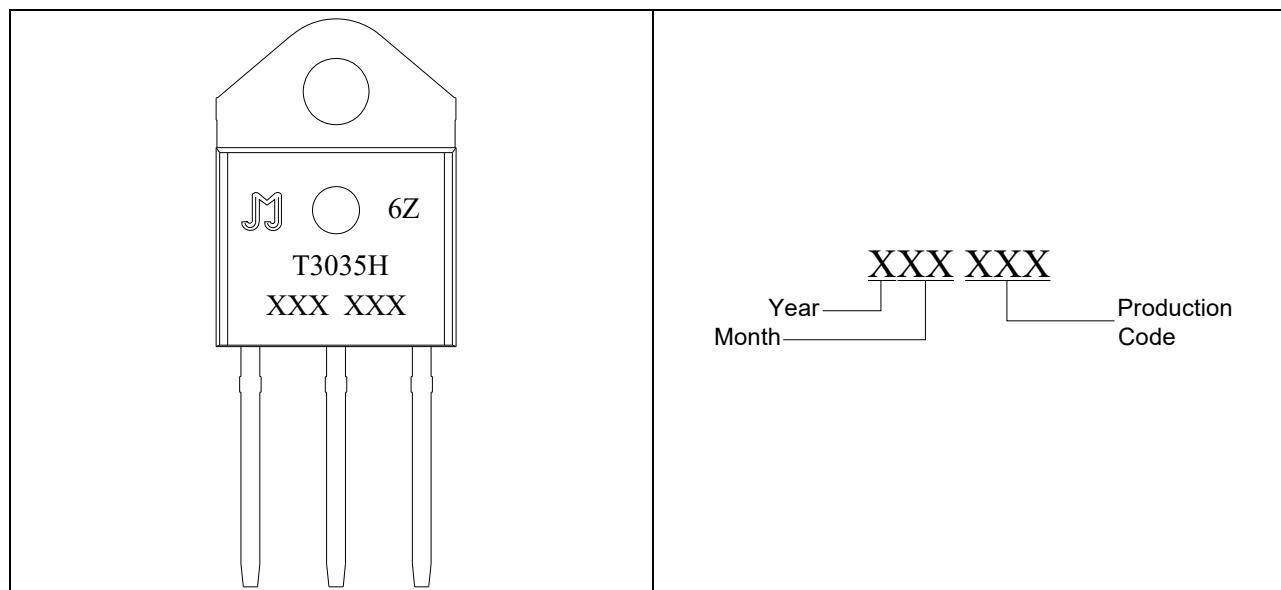
MARKING

FIG.1 Maximum power dissipation versus RMS on-state current

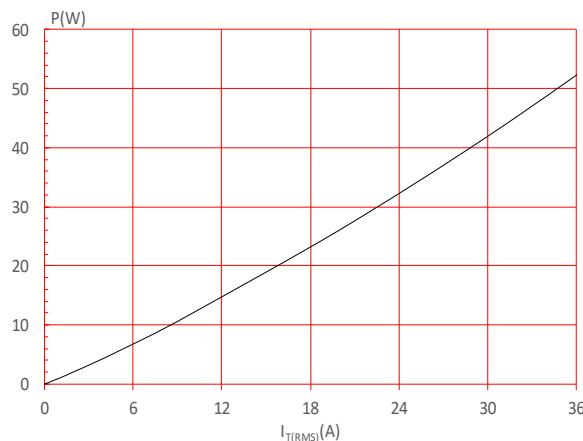


FIG.3: Surge peak on-state current versus number of cycles

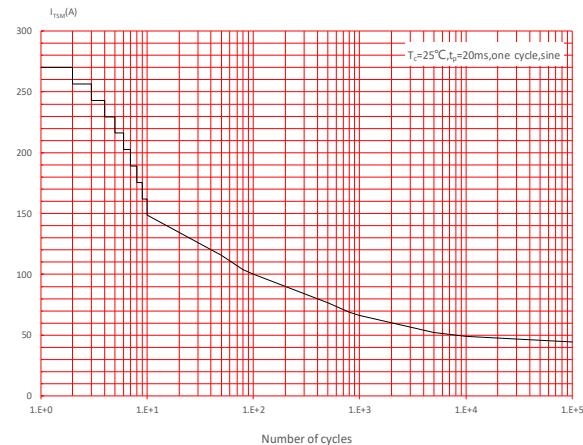


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($dI/dt < 100\text{A}/\mu\text{s}$)

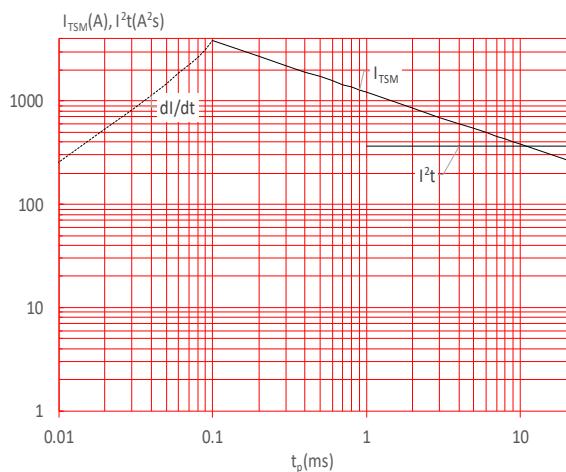


FIG.2: RMS on-state current versus case temperature

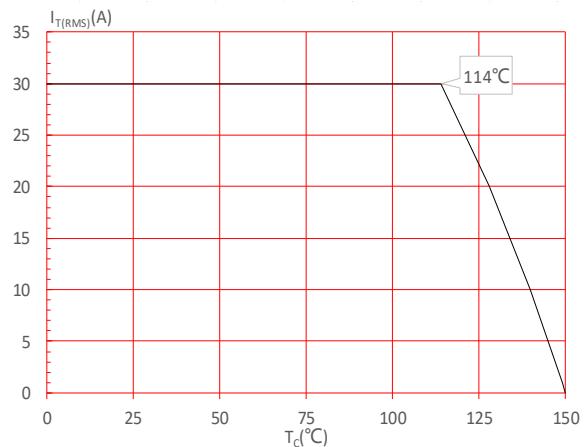


FIG.4: On-state characteristics

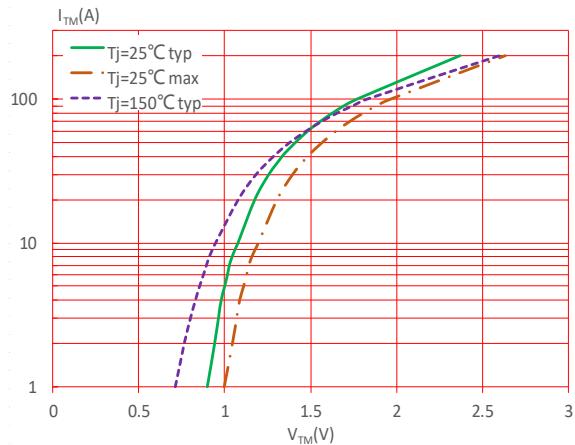


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

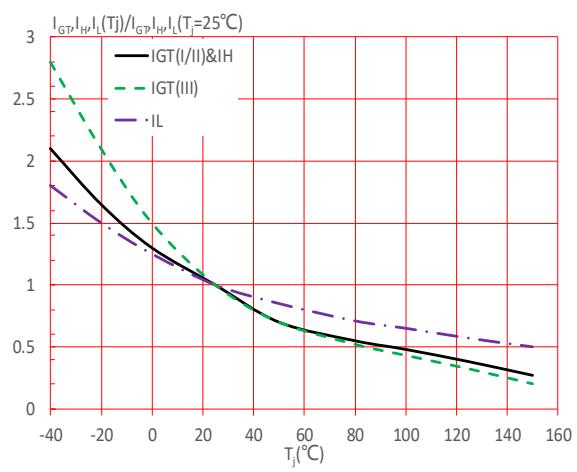
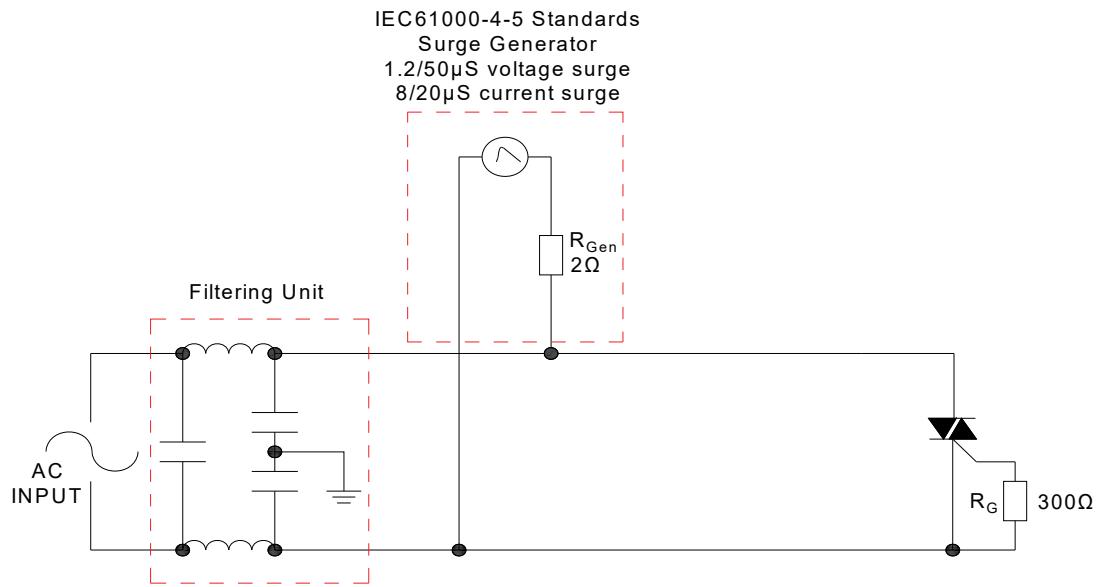


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

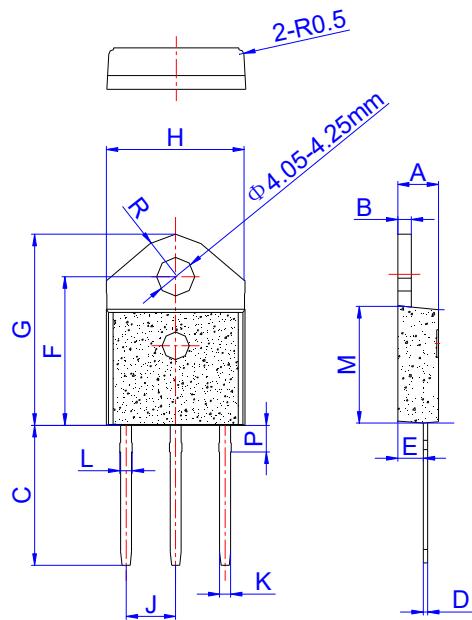
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I -II-III			
T3035H-6Z	600	35	TO-3P(Ins)	30	Tube

Document Revision History

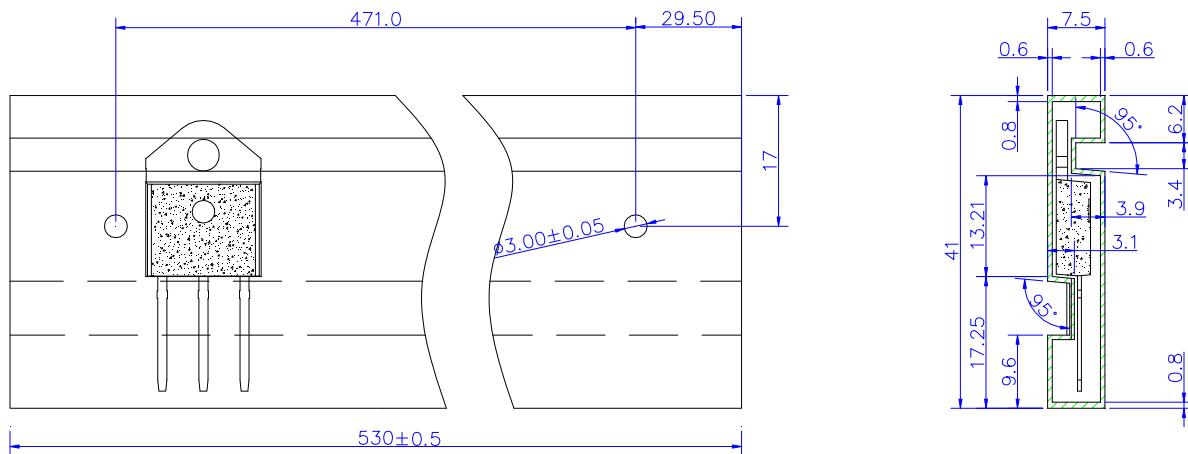
Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.25		1.45	0.049		0.057
M	12.37		12.77	0.487		0.503
P	2.80		3.00	0.110		0.118
R		4.35			0.171	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-3P	TUBE	30	450	2,250

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